

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

TMD0507-2A

FEATURES

- High Power
P1dB=33dBm at 5.1 to 7.2GHz
- High Gain
G1dB=22dB at 5.1 to 7.2GHz
- Broadband Internally Matched
- Hermetically Sealed Package

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATINGS
DRAIN SUPPLY VOLTAGE	VDD	V	15
GATE SUPPLY VOLTAGE	VGG	V	-10
INPUT POWER	Pin	W	0.3
FLANGE TEMPERATURE	Tf	°C	-30 - +80
STORAGE TEMPERATURE	Tstg	°C	-65+ - +175

RF PERFORMANCE SPECIFICATIONS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDD1=VDD2 =VDD3=10V Vgg=-5V F=5.1 - 7.2 GHz	dBm	32.0	33.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	20.0	22.0	—
Gain Flatness (1)*	ΔG1		dB	—	—	+/-1.5
Gain Flatness (2)**	ΔG2		dB	—	—	+/-2.0
Drain Current ***	IDD		A	—	1.60	1.90
VSWRin(small signal)	VSWRin		—	—	—	3.0

*ΔG at f=5.9 - 7.2GHz

**ΔG at f=5.1 - 7.2GHz

***IDD=IDD1+IDD2+IDD3

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PACKAGE OUTLINE (2-11E1A)

